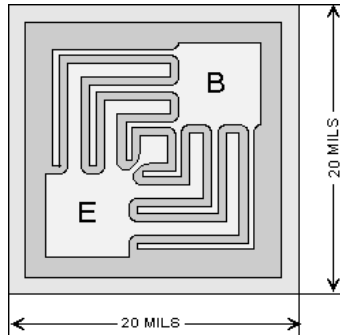


**Chip Type 2C2907A**  
**Geometry 0600**  
**Polarity PNP**

**Generic Packaged Parts:**

**2N2905, 2N2905A, 2N2907,  
 2N2907A**



[Request Quotation](#)

Chip type **2C2907A** by Semicoa Semiconductors provides performance similar to these devices.

**Part Numbers:**

2N2905, [2N2905A](#), [2N2905AL](#), 2N2907, [2N2907A](#),  
[2N2907AUB](#), SD2907A, SD2907AF, SQ2907A,  
 SQ2907AF, 2N3486, 2N3486A, 2N6987, 2N6989

**Product Summary:**

**APPLICATIONS:** Designed for general purpose switching and amplifier applications.

**Features:** [Radiation graphs available](#)

### Mechanical Specifications

<b>Metallization</b>	Top	Al - 18 kÅ min.
	Backside	Au - 6.5 kÅ nom.
<b>Bonding Pad Size</b>	Emitter	4.0 mils x 4.0 mils
	Base	4.0 mils x 4.0 mils
<b>Die Thickness</b>	8 mils nominal	
<b>Chip Area</b>	20 mils x 20 mils	
<b>Top Surface</b>	Silox Passivated	

### Electrical Characteristics

$T_A = 25^\circ\text{C}$

Parameter	Test conditions	Min	Max	Unit
$BV_{CEO}$	$I_C = 10 \text{ mA}, I_B = 0$	60	---	V dc
$BV_{CBO}$	$I_C = 10 \text{ }\mu\text{A}, I_E = 0$	60	---	V dc
$BV_{EBO}$	$I_E = 10 \text{ }\mu\text{A}, I_C = 0$	5.0	---	V dc
$I_{CBO}$	$V_{CB} = 50 \text{ V}, I_E = 0$	---	10	nA
$h_{FE}$	$I_C = 150 \text{ mA dc}, V_{CE} = 10 \text{ V}$	100	300	---

*Due to limitations of probe testing, only dc parameters are tested. This must be done with pulse width less than 300  $\mu\text{s}$ , duty cycle less than 2%.*